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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/707,396	12/10/2003	Ching-Nan Hsiao	NTCP0020USA	1395
27765	7590	09/09/2005	EXAMINER	
NORTH AMERICA INTELLECTUAL PROPERTY CORPORATION P.O. BOX 506 MERRIFIELD, VA 22116			GEBREMARIAM, SAMUEL A	
			ART UNIT	PAPER NUMBER
			2811	

DATE MAILED: 09/09/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/707,396

Applicant(s)

HSIAO ET AL.

AK

Examiner

Samuel A. Gebremariam

Art Unit

2811

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 24 June 2005.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-29 is/are pending in the application.
- 4a) Of the above claim(s) 17-29 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-16 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

DETAILED ACTION

1. Newly submitted claims 17-29 are directed to an invention that is independent or distinct from the invention originally claimed for the following reasons: Claims 17-29 are related to a process of making a vertical DRAM which distinct from the original claims 1-13 that are related to a structure of vertical DRAM.

Since applicant has received an action on the merits for the originally presented invention, this invention has been constructively elected by original presentation for prosecution on the merits. Accordingly, claims 17-29 are withdrawn from consideration as being directed to a non-elected invention. See 37 CFR 1.142(b) and MPEP § 821.03.

Claim Rejections - 35 USC § 112

2. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 14 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. It is not clear as to what applicant is trying to claim when stating "the second contact plug further contacts the STI at a first side of the second contact plug while contacts the annular spacer at a second side of the second contact plug, the second side being opposite to the first side of the second contact plug".

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Art Unit: 2811

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 1-12 and 15-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mandelman et al. US patent No. 6,605,838, in view of Dyer, US patent No. 6,747,306.

Regarding claim 1, Mandelman teaches (fig. 2) a vertical dynamic random access memory (DRAM) comprising: a substrate (50) comprising at least a deep trench (56) having an upper trench portion (region where element 80 is formed) and a lower trench portion (region where element 70 is formed); a trench capacitor (70) located in the lower trench portion; a source-isolation oxide layer (88, referred here trench top oxide) located on the trench capacitor (70); and a vertical transistor (80) located on the source-isolation oxide layer (88), the vertical transistor comprising: an annular source (86) set in the substrate next to the source-isolation oxide layer (88), the annular source being electrically connected to the trench capacitor (fig. 2); a gate conductive layer (84) filling the upper trench portion; a cylindrical gate dielectric layer (82) located on a surface of a sidewall of the upper trench portion and circularly encompassing the gate conductive layer; and an annular drain (52) circularly encompassing the deep trench near a surface of the substrate (50).

Mandelman does not explicitly teach that a shallow trench isolation (STI) positioned around the deep trench; the gate conductive layer is electrically connected to a first contact plug and the annular drain being electrically connected to a second contact plug and the annular trench positioned next to the STI, the STI completely

Art Unit: 2811

compassing the vertical transistor and separating the annular drain from other annular drains of any adjacent vertical transistor in the substrate.

It is conventional and also taught by Dyer (figs. 1 and 4) forming contact structure (122) on a gate conductive layer (114) and also making contact structure (134) on a drain region (118) in order to make contact to other portion of an integrated circuit device. Dyer also teaches (fig. 4) the use of STI structures (206), the STI completely compassing the vertical transistor (also refer fig. 1, 124) and separating the annular drain (118) from other annular drains of any adjacent vertical transistor in the substrate.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the gate and drain contact in the structure taught by Dyer in the structure of Mandelman in order to make contact to other portion of the integrated circuit. Furthermore it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the STI structures taught by Dyer in the structure of Mandelman in order to provide better isolation. The modified structure of Mandelman and Dyer would have an STI structure, where the STI completely compassing the vertical transistor and separating the annular drain from other annular drains of any adjacent vertical transistor in the substrate.

Regarding claim 2, Mandelman teaches substantially the entire claimed structure of claim 1 above including a storage node filling (68) the lower trench portion and electrically connected to the annular source (86); a capacitor dielectric layer (66) encompassing the storage node; and a buried plate (64) located in the substrate in a side of the capacitor dielectric layer.

Art Unit: 2811

Regarding claim 3, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including the buried plate (64) surrounds a sidewall of the lower trench portion, and the capacitor dielectric layer (66) is located on a surface of the sidewall of the lower trench portion so as to isolate the storage node and the buried plate.

Regarding 4, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including the trench capacitor further comprises a buried strap (86) for electrically connecting the annular source and the storage node (col. 5, lines 10-20).

Regarding claim 5, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including the buried strap (86, col. 5, lines 10-20) is an annular conductive strap located on the surface of the sidewall of the lower trench portion above the capacitor dielectric layer (66).

Regarding claim 6, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including a conductive layer (122) located on the gate conductive layer (114, Dyer) for electrically connecting the gate conductive layer and the first contact plug.

The combined structure of Mandelman and Dyer provides conductive layer located on the gate conductive layer for electrically connecting the gate conductive layer (metallization layers or metal lines) and the first contact plug.

Art Unit: 2811

Regarding claim 7, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including the annular source is an ion diffusion area (col. 5, lines 10-20).

Regarding claim 8, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including the annular drain is a heavily doped area.

The limitation that annular drain overlaps ion implantation area is not given patentable weight, because it is product by process claim. "[E]ven though product-by process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." *In re Thorpe*, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985).

Regarding claim 9, Mandelman teaches substantially the entire claimed structure of claim 1 above including a passivation layer (132, Dyer) covering the surface of the substrate and the transistor.

Regarding claim 10, Mandelman teaches (fig. 2) substantially the entire claimed structure of claim 1 above including the first and the second contact plug are electrically connected to a word line and a bit line respectively (col. 9, lines 1-5, Mandelman).

Regarding claim 11, Mandelman teaches substantially the entire claimed structure of claim 1 above the STI surrounds the annular source and the annular drain region without overlapping the deep trench (figs. 1 and 4 of Dyer).

Regarding claim 12, Mandelman teaches substantially the entire claimed structure of claim 1 above including an annular spacer (126) surrounding the upper portion (refer to fig. 1, Dyer).

Regarding claim 15, Mandelman teaches substantially the entire claimed structure of claim 1 above including the annular spacer (126, Dyer, fig. 1) positioned on an outer surface of the sidewall of the entire upper trench portion.

Regarding claim 16, Mandelman teaches substantially the entire claimed structure of claim 1 above except explicitly stating that the annular drain positioned below the second contact plug having a larger width from the STI to the deep trench than a width of a portion of the annular drain not positioned below the second contact plug.

Parameters such as thickness and width in the art of semiconductor manufacturing process are subject to routine experimentation and optimization to achieve the desired device characteristics during fabrication.

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust the width of the annular drain as claimed in order to make appropriate contact for further integration.

5. Claims 13 is rejected under 35 U.S.C. 103(a) as being unpatentable over Mandelman et al. US patent No. 6,605,838, in view of Ozaki, US patent No. 5,519,236.

Regarding claim 13, Mandelman teaches substantially the entire claimed structure of claim 1 above except explicitly stating that the second contact plug has an

Art Unit: 2811

asymmetric structure, which is positioned on the spacer and the drain while contacts the spacer and the drain at the same time.

Ozaki teaches (fig. 2A) an asymmetric contact plug, which is positioned on the spacer (23) and the drain (24) while contacts the spacer and the drain at the same time (fig. 2A).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the asymmetric contact plug structure taught by Ozaki in the combined structure of Mandelman and Dyer in order to make contact structure for further integrating the device.

Response to Arguments

6. Applicant's arguments with respect to claims 1-13 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Samuel A. Gebremariam whose telephone number is (571) 272-1653. The examiner can normally be reached on 8:00am-4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Steve Loke can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 2811

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

SAG
September 6, 2005

Steven Loke
Primary Examiner

A handwritten signature in black ink, appearing to read "Steven Loke", written in a cursive style.